

TSMC-01-714



April 3, 2002

Commissioner of Patents and Trademarks
Washington, D.C. 20231

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Subject:

Serial No. 10/054,561 01/22/02

Bor-Wen Chan et al.

A METHOD OF FORMING A STACKED
CAPACITOR STRUCTURE WITH INCREASED
SURFACE AREA FOR A DRAM DEVICE

Grp. Art Unit: 1765

INFORMATION DISCLOSURE STATEMENT

Enclosed is Form PTO-1449, Information Disclosure Citation
In An Application.

The following Patents and/or Publications are submitted to
comply with the duty of disclosure under CFR 1.97-1.99 and
37 CFR 1.56. Copies of each document is included herewith.

CERTIFICATE OF MAILING

I hereby certify that this correspondence is being
deposited with the United States Postal Service as first class
mail in an envelope addressed to: Commissioner of Patents and
Trademarks, Washington, D.C. 20231, on April 3, 2002.

Stephen E. Ackerman, Reg.# 37761

Signature-Date

U.S. Patent 6,025,225 to Forbes et al., "Circuits with a Trench Capacitor Having Micro-Roughened Semiconductor Surfaces and Methods for Forming the Same," discloses a trench cap process with roughened sides.

U.S. Patent 5,923,989 to Lin et al., "Method of Fabricating Rugged Capacitor of High Density DRAMs," reveals a stacked Cap process with Hemispherical grains (HSG).

U.S. Patent 5,691,221 to Jun, "Method for Manufacturing Semiconductor Memory Device Having a Stacked Capacitor," discloses a fin capacitor.

U.S. Patent 5,670,405 to Tseng, "Method of Making a Tooth Shaped Capacitor Using Ion Implantation," discloses a method of manufacturing a capacitor for use in semiconductor memories.

U.S. Patent 5,801,089 to Kenney, "Method of Forming Stacked Devices," discloses chips having subsurface structures within or adjacent to a horizontal trench in bulk single crystal semiconductors.

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U.S. Patent 6,057,205 to Wu, "Method to Form a Ragged Poly-Si Structure for High Density DRAM Cells," discloses a method for fabricating a capacitor on a semiconductor device.

Sincerely,

A handwritten signature in dark ink, appearing to read "S. B. Ackerman", with a horizontal line above the first name.

Stephen B. Ackerman, Reg. #37761

(Use several sheets if necessary)

APR 15 2002

U. S. PATENT DOCUMENTS

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Aggravated!

Bor-Wen Chan et al.

<p> Filing Date 11/11/2011 </p>	<p> Page 1 </p>
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EXAMINER
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DOCUMENT NUMBER

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CLASS

RESULTS

HOUSE OF REPRESENTATIVES

6025225215/00	Forbes et al.	438	243	1/22/98
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56704059/23/97	Tseng	437	52	1/30/97
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FOREIGN PATENT DOCUMENTS

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OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

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